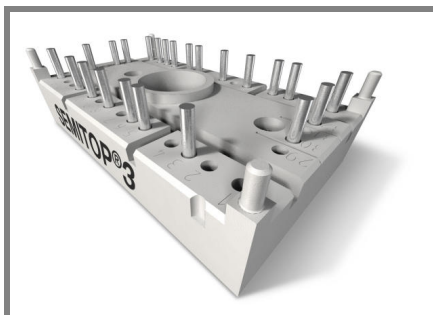


SK100GB066T



SEMITOP® 3

IGBT Module

SK100GB066T

Target Data

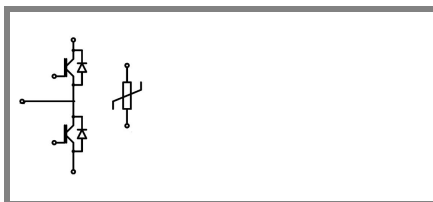
Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{isol} = 3000V$ AC, 50Hz, 1s

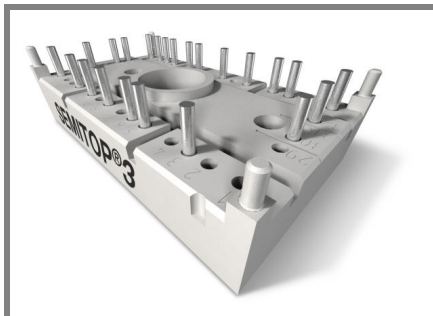


GB-T

| Absolute Maximum Ratings | | $T_s = 25\text{ °C}$, unless otherwise specified | | |
|--------------------------|---|---|-----|-------|
| Symbol | Conditions | Values | | Units |
| IGBT | | | | |
| V_{CES} | $T_j = 25\text{ °C}$ | 600 | | V |
| I_C | $T_j = 175\text{ °C}$ | $T_s = 25\text{ °C}$ | 96 | |
| | | $T_s = 70\text{ °C}$ | 75 | |
| I_{CRM} | $I_{CRM} = 2 \times I_{Cnom}$ | 200 | | A |
| V_{GES} | | ± 20 | | V |
| t_{psc} | $V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 150\text{ °C}$ $V_{CES} < 600\text{ V}$ | 6 | | µs |
| Inverse Diode | | | | |
| I_F | $T_j = 175\text{ °C}$ | $T_s = 25\text{ °C}$ | 108 | |
| | | $T_s = 70\text{ °C}$ | 84 | |
| I_{FRM} | $I_{FRM} = 2 \times I_{Fnom}$ | 200 | | A |
| Module | | | | |
| $I_{t(RMS)}$ | | | | A |
| T_{vj} | | -40 ... +175 | | °C |
| T_{stg} | | -40 ... +125 | | °C |
| V_{isol} | AC, 1 min. | 2500 | | V |

| Characteristics | | $T_s = 25\text{ °C}$, unless otherwise specified | | | |
|-----------------|--|---|--------|------|-------|
| Symbol | Conditions | min. | typ. | max. | Units |
| IGBT | | | | | |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}, I_C = 1,6\text{ mA}$ | 5 | 5,8 | 6,5 | V |
| I_{CES} | $V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ | $T_j = 25\text{ °C}$ | 0,0026 | | mA |
| | | $T_j = 125\text{ °C}$ | | | mA |
| I_{GES} | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$ | $T_j = 25\text{ °C}$ | 1200 | | nA |
| V_{CE0} | | $T_j = 25\text{ °C}$ | 0,8 | 1,1 | V |
| | | $T_j = 125\text{ °C}$ | 0,7 | 1 | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ | $T_j = 25\text{ °C}$ | 6,5 | 8 | mΩ |
| | | $T_j = 150\text{ °C}$ | 9,5 | 10,5 | mΩ |
| $V_{CE(sat)}$ | $I_{Cnom} = 100\text{ A}, V_{GE} = 15\text{ V}$ | $T_j = 25\text{ °C}_{chiplev.}$ | 1,45 | 1,85 | V |
| | | $T_j = 150\text{ °C}_{chiplev.}$ | 1,65 | 2,05 | V |
| C_{ies} | $V_{CE} = 25, V_{GE} = 0\text{ V}$ | 6,28 | | nF | |
| C_{oes} | | 0,4 | | nF | |
| C_{res} | | 0,19 | | nF | |
| Q_G | $V_{GE} = -7V...+15V$ | 1000 | | nC | |
| $t_{d(on)}$ | $R_{Gon} = 32\text{ }\Omega$ $di/dt = 2575\text{ A}/\mu\text{s}$ | $V_{CC} = 300V$ $I_C = 100A$ | 144 | | ns |
| t_r | | | 128 | | ns |
| E_{on} | | | 7 | | mJ |
| $t_{d(off)}$ | $R_{Goff} = 32\text{ }\Omega$ $di/dt = 2575\text{ A}/\mu\text{s}$ | $T_j = 150\text{ °C}$ $V_{GE} = -7/+15V$ | 1040 | | ns |
| t_f | | | 91 | | ns |
| E_{off} | | | 6 | | mJ |
| $R_{th(j-s)}$ | per IGBT | 0,78 | | K/W | |

SK100GB066T



SEMITOP[®] 3

IGBT Module

SK100GB066T

Target Data

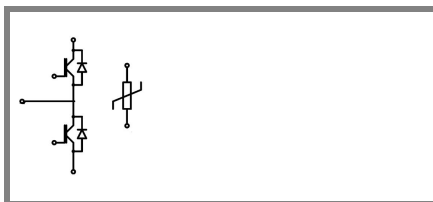
Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{isol} = 3000V$ AC, 50Hz, 1s

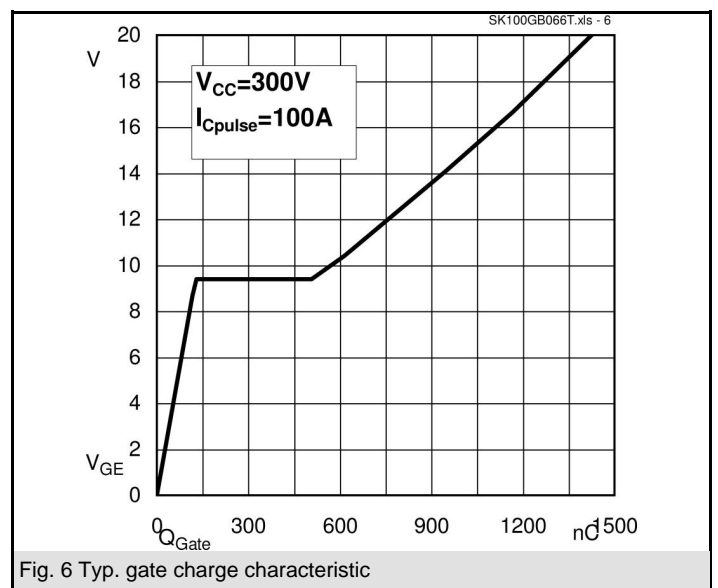
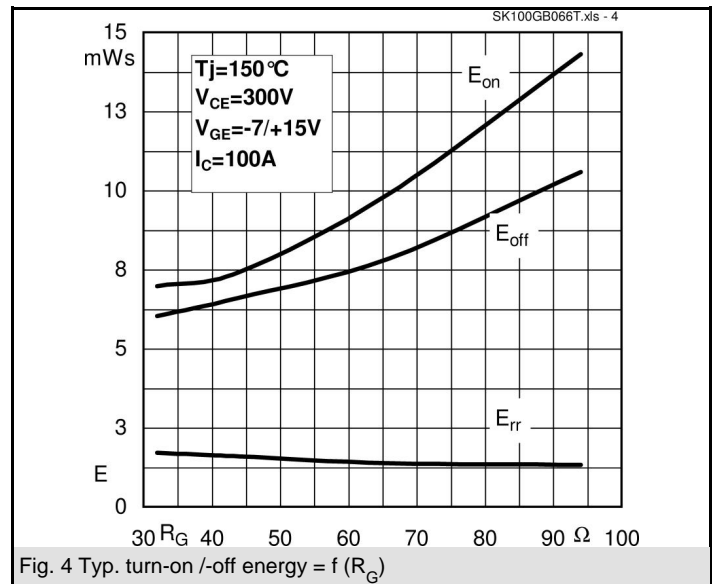
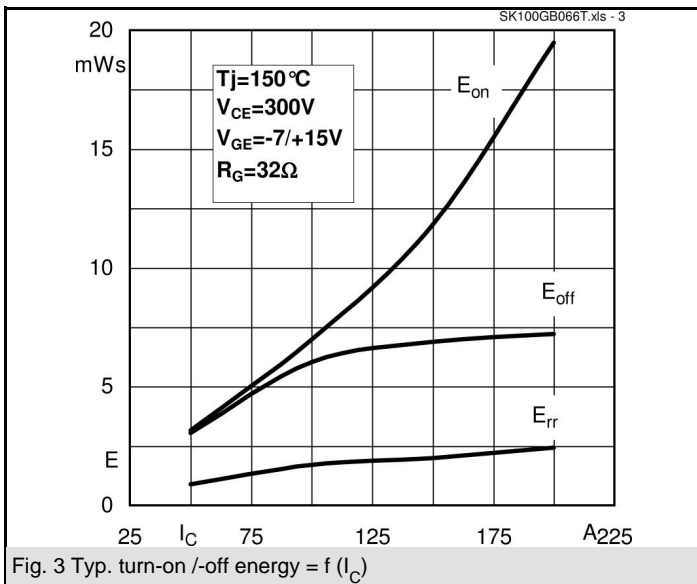
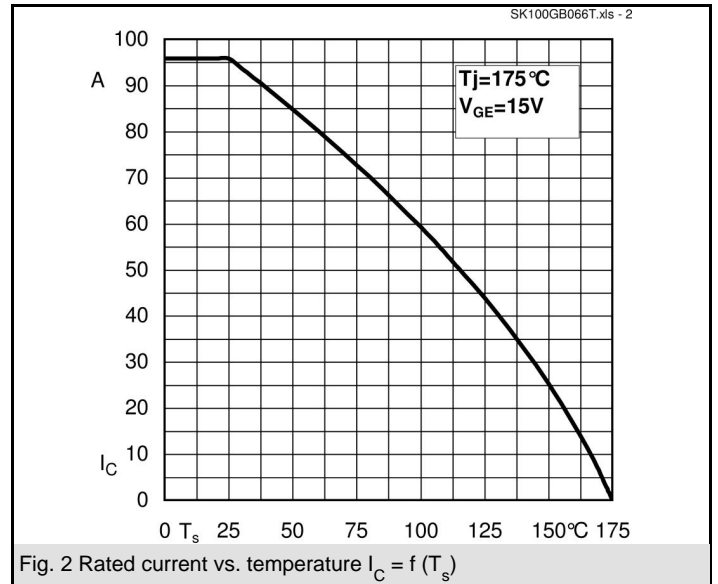
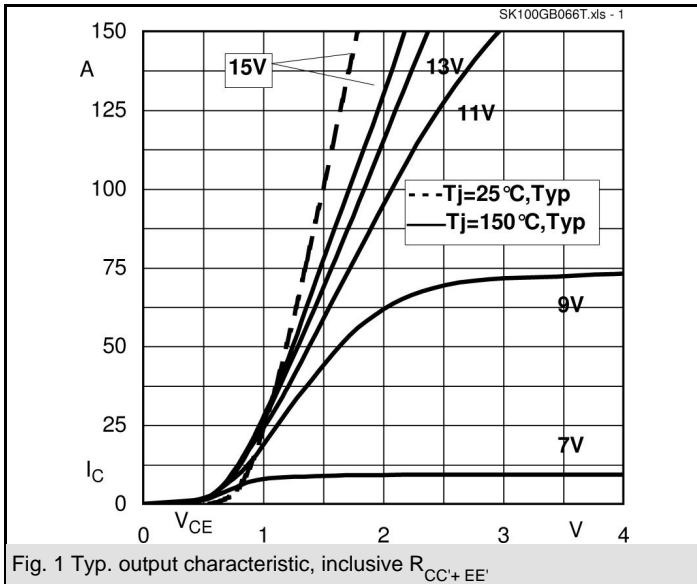


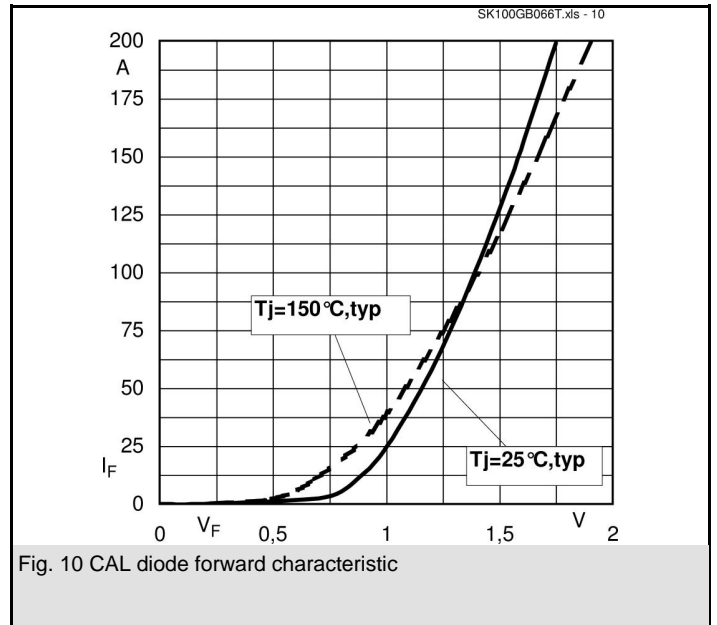
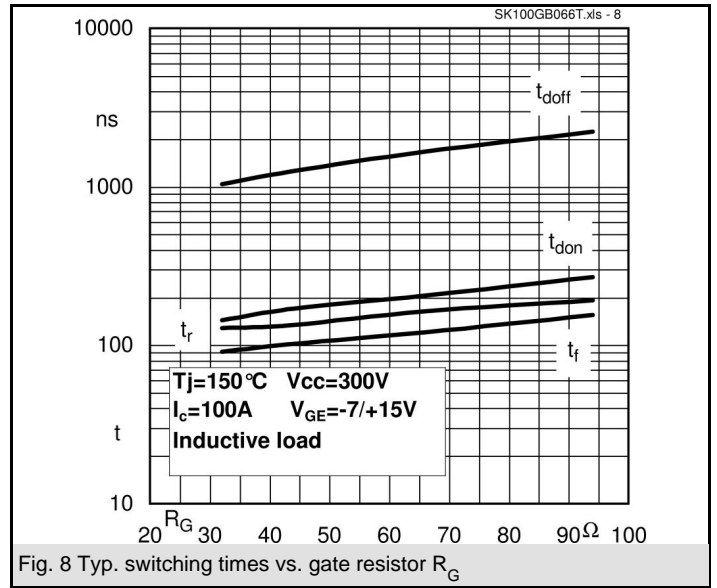
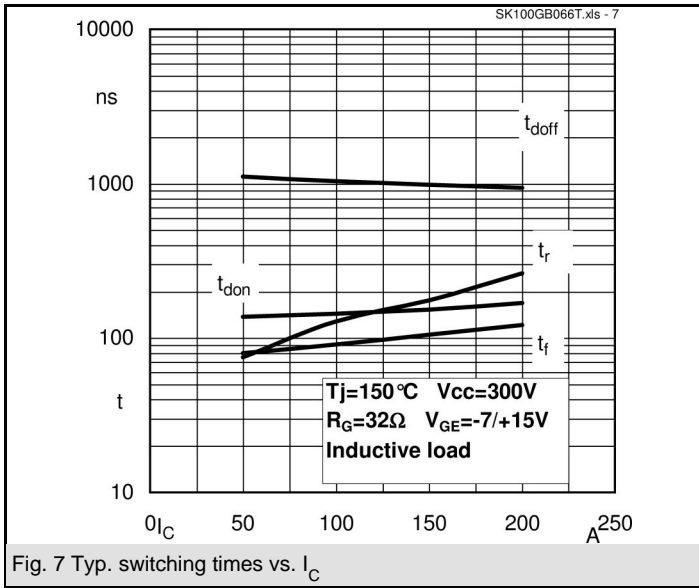
GB-T

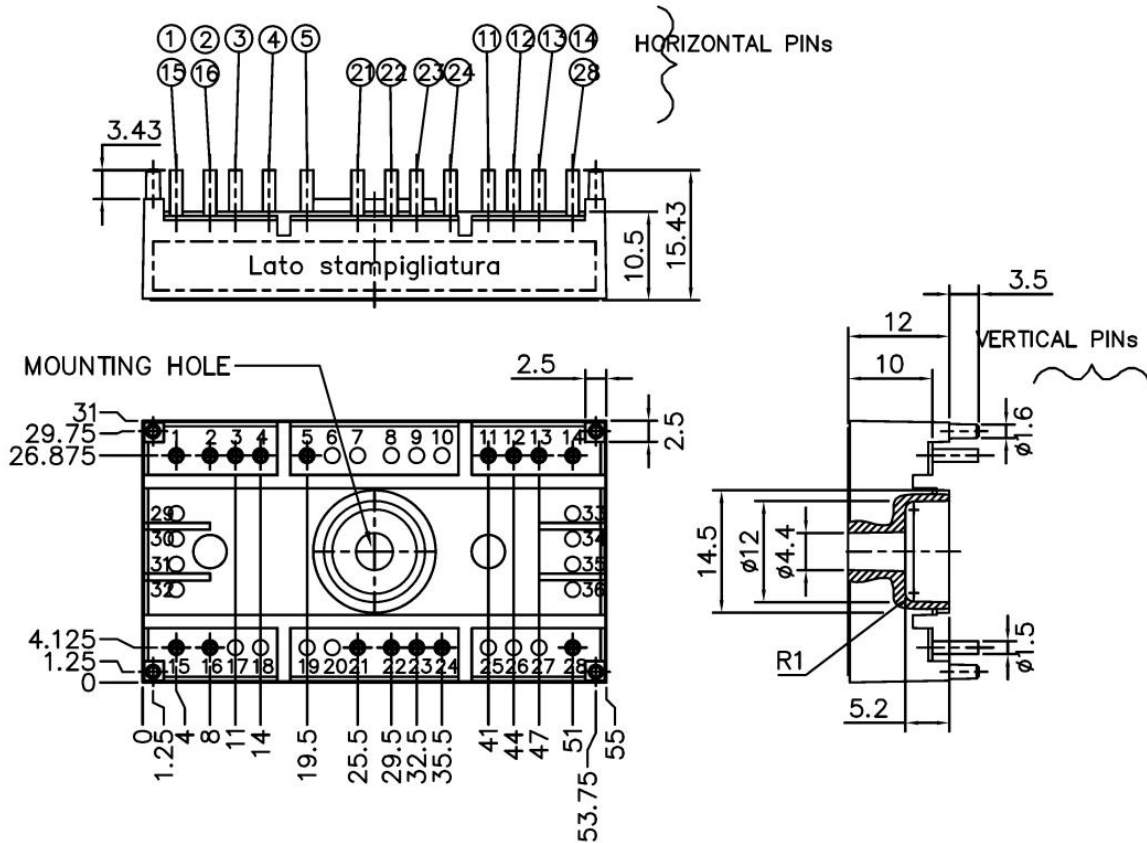
| Characteristics | | | | | |
|---------------------------|---|---------------------------------|--------|------|-------|
| Symbol | Conditions | min. | typ. | max. | Units |
| Inverse Diode | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom} = 100 A; V_{GE} = 0 V$ | $T_j = 25 ^\circ C_{chiplev.}$ | 1,35 | | V |
| | | $T_j = 150 ^\circ C_{chiplev.}$ | 1,31 | | V |
| V_{F0} | | $T_j = 25 ^\circ C$ | | | V |
| | | $T_j = 150 ^\circ C$ | 0,85 | | V |
| r_F | | $T_j = 25 ^\circ C$ | | | mΩ |
| | | $T_j = 150 ^\circ C$ | 6,3 | | mΩ |
| I_{RRM} | $I_F = 100 A$ | $T_j = 150 ^\circ C$ | 60 | | A |
| Q_{rr} | $di/dt = 2575 A/\mu s$ | | 5,6 | | μC |
| E_{rr} | $V_R = 300V$ | | 1,7 | | mJ |
| $R_{th(j-s)D}$ | per diode | | 0,91 | | K/W |
| Freewheeling Diode | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom} = A; V_{GE} = V$ | $T_j = ^\circ C_{chiplev.}$ | | | V |
| V_{F0} | | $T_j = ^\circ C$ | | | V |
| r_F | | $T_j = ^\circ C$ | | | V |
| I_{RRM} | $I_F = A$ | $T_j = ^\circ C$ | | | A |
| Q_{rr} | | | | | μC |
| E_{rr} | $V_R = 300V$ | | | | mJ |
| $R_{th(j-s)FD}$ | per diode | | | | K/W |
| M_s | to heat sink | | 2,5 | 2,75 | Nm |
| w | | | 60 | | g |
| Temperature sensor | | | | | |
| R_{100} | $T_s = 100^\circ C (R_{25} = 5k\Omega)$ | | 493±5% | | Ω |

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T 73 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)

